SNx4LVC08A Quadruple 2-Input Positive-AND Gates

1 Features

- Latch-up performance exceeds 250mA per JESD 17
- ESD protection exceeds JESD 22
  - 2000V Human-Body Model (A114-A)
  - 1000V Charged-Device Model (C101)
  - On products compliant to MIL-PRF-38535, All parameters are tested unless otherwise noted. On all other products, production processing does not necessarily include testing of all parameters.
- SN74LVC08A operates from 1.65V to 3.6V
- SN54LVC08A operates from 2.0V to 3.6V
- SNx4LVC08A specified from –40°C to +85°C and –40°C to +125°C
- SN54LVC08A specified from –55°C to +125°C
- Inputs accept voltages to 5.5V
- Max t_{pd} of 4.1ns at 3.3V
- Typical V_{OLP} (output ground bounce) <0.8V at V_{CC} = 3.3V, T_A = 25°C
- Typical V_{OHV} (output V_{OH} undershoot) >2V at V_{CC} = 3.3V, T_A = 25°C

2 Applications

- Servers
- LED Displays
- Network Switches
- I/O Expanders
- Base Station Processor Board

3 Description

The SN54LVC08A quadruple 2-input positive-AND gate is designed for 2.7V to 3.6V V_{CC} operation, and the SN74LVC08A quadruple 2-input positive-AND gate is designed for 1.65V to 3.6V V_{CC} operation.

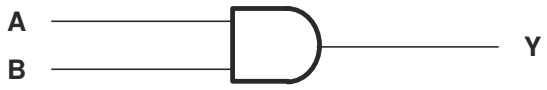
The SNx4LVC08A devices perform the Boolean function $Y = A \bullet B$ or $Y = \overline{\overline{A} + \overline{B}}$ in positive logic.

Inputs can be driven from either 3.3V or 5V devices. This feature allows the use of these devices as translators in a mixed 3.3V/5V system environment.

Device Information

PART NUMBER	PACKAGE(1)	PACKAGE SIZE(2)	BODY SIZE(3)
SNx4LVC08A	BQA (WQFN, 14)	3mm × 2.5mm	3mm × 2.5mm
	D (SOIC, 14)	8.65mm × 6mm	8.65mm × 3.91mm
	DB (SSOP, 14)	6.2mm × 7.8mm	6.20mm × 5.30mm
	NS (SOP, 14)	10.2mm × 7.8mm	10.30mm × 5.30mm
	PW (TSSOP, 14)	5mm × 4.4mm	5.00mm × 4.40mm
	RGY (VQFN, 14)	3.5mm × 3.5mm	3.50mm × 3.50mm
	FK (LCCC, 20)	8.9mm x 8.9mm	8.89mm × 8.89mm
	J (CDIP, 14)	19.55mm x 7.9mm	19.55mm x 6.7mm
	W (CFP, 14)	9.21mm x 9mm	9.21mm x 6.28mm

(1) For more information, see Section 11.
(2) The package size (length × width) is a nominal value and includes pins, where applicable.
(3) The body size (length × width) is a nominal value and does not include pins.



Logic Diagram, Each Gate (Positive Logic)

Table of Contents

4 Pin Configuration and Functions

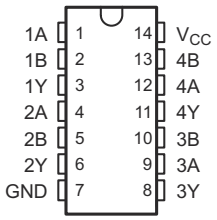


Figure 4-1. D, DB, NS, J, W, or PW Package 14-Pin SOIC, SSOP, SOP, CDIP, or TSSOP (Top View)

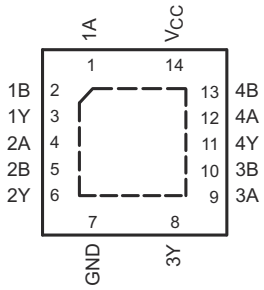


Figure 4-2. BQA or RGY Package 14-Pin WQFN or VQFN (Top View)

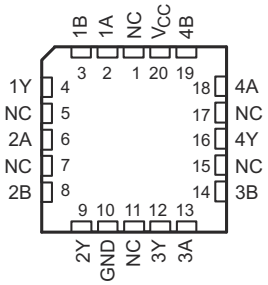


Figure 4-3. FK Package 20-Pin LCCC (Top View)

Table 4-1. Pin Functions

PIN			TYPE	DESCRIPTION
NAME	SOIC, SSOP, SOP, CDIP, TSSOP, VQFN,WQFN	LCCC		
1A	1	2	I	Channel 1 input A
1B	2	3	I	Channel 1 input B
1Y	3	4	O	Channel 1 output
2A	4	6	I	Channel 2 input A
2B	5	8	I	Channel 2 input B
2Y	6	9	O	Channel 2 output
GND	7	10	Ground	Ground
3Y	8	12	O	Channel 3 output
3A	9	13	I	Channel 3 input A
3B	10	14	I	Channel 3 input B
4Y	11	16	O	Channel 4 output
4A	12	18	I	Channel 4 input A
4B	13	19	I	Channel 4 input B
V_{CC}	14	20	Power	Positive supply
Thermal Information(1)			—	The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply.
NC(2)	—	1	—	No connect
		5		
		7		
		11		
		15		
		17		

(1) For BQA package only.
(2) NC – No internal connection

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	6.5	V
V_I	Input voltage(2)		–0.5	6.5	V
V_O	Output voltage(2) (3)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		–50	mA
I_{OK}	Output clamp current	V_O < 0		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
P_{tot}	Power dissipation(4) (5)	T_A = –40°C to +125°C		500	mW
T_J	Junction temperature		–65	150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
(3) The value of V_{CC} is provided in the *Recommended Operating Conditions* table.
(4) For the D package: above 70°C, the value of P_{tot} derates linearly with 8 mW/K.
(5) For the DB, NS, and PW packages: above 60°C, the value of P_{tot} derates linearly with 5.5 mW/K.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	
		Machine Model (MM) A115-A	200	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions, SN54LVC08A

over operating free-air temperature range (unless otherwise noted)(1)

			SN54LVC08A		UNIT
			–55°C to +125°C		
			MIN	MAX	
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7V to 3.6V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7V to 3.6V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7V		–12	mA
		V_{CC} = 3V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7V		12	mA
		V_{CC} = 3V		24	
Δt/Δv	Input transition rise or fall rate			8	ns/V

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*, SCBA004.

5.4 Recommended Operating Conditions, SN74LVC08A

See(1)

			SN74LVC08A						UNIT
			T_A = 25°C		–40°C to +85°C		–40°C to +125°C		
			MIN	MAX	MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	Operating	1.65	3.6	1.65	3.6	1.65	3.6	V
		Data retention only	1.5		1.5		1.5		
V_{IH}	High-level input voltage	V_{CC} = 1.65V to 1.95V	0.65 × V_{CC}		0.65 × V_{CC}		0.65 × V_{CC}		V
		V_{CC} = 2.3V to 2.7V	1.7		1.7		1.7		
		V_{CC} = 2.7V to 3.6V	2		2		2		
V_{IL}	Low-level input voltage	V_{CC} = 1.65V to 1.95V		0.35 × V_{CC}		0.35 × V_{CC}		0.35 × V_{CC}	V
		V_{CC} = 2.3V to 2.7V		0.7		0.7		0.7	
		V_{CC} = 2.7V to 3.6V		0.8		0.8		0.8	
V_I	Input voltage		0	5.5	0	5.5	0	5.5	V
V_O	Output voltage		0	V_{CC}	0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 1.65V		–4		–4		–4	mA
		V_{CC} = 2.3V		–8		–8		–8	
		V_{CC} = 2.7 V		–12		–12		–12	
		V_{CC} = 3V		–24		–24		–24	
I_{OL}	Low-level output current	V_{CC} = 1.65V		4		4		4	mA
		V_{CC} = 2.3V		8		8		8	
		V_{CC} = 2.7V		12		12		12	
		V_{CC} = 3V		24		24		24	
Δt/Δv	Input transition rise or fall rate			8		8		8	ns/V

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*, SCBA004.

5.5 Thermal Information

THERMAL METRIC(1)		SN74LVC08A						UNIT
		BQA (WQFN)	D (SOIC)	DB (SSOP)	NS (SO)	PW (TSSOP)	RGY (LCCC)	
		14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	102.3	98.6	140.4	123.8	150.8	92.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	96.8	56.0	65.3	52.7	56.0	56.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	70.9	53.3	60.2	53.9	69.5	27.5	°C/W
ψ_{JT}	Junction-to-top characterization parameter	16.6	16.4	25.3	17.9	8.9	4.5	°C/W
ψ_{JB}	Junction-to-board characterization parameter	70.9	53.0	59.6	53.6	68.9	27.7	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	50.1	—	—	—	—	19.1	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

5.6 Electrical Characteristics, SN54LVC08A

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN54LVC08A –55°C to +125°C			UNIT
			MIN	TYP(1)	MAX	
V_{OH}	I_{OH} = –100 µA	2.7V to 3.6V	V_{CC} – 0.2			V
	I_{OH} = –12 mA	2.7V	2.2			
		3V	2.4			
	I_{OH} = –24 mA	3V	2.2			
V_{OL}	I_{OL} = 100 µA	2.7V to 3.6V			0.2	V
	I_{OL} = 12 mA	2.7V			0.4	
	I_{OL} = 24 mA	3V			0.55	
I_I	V_I = 5.5 V or GND	3.6V			±5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7V to 3.6V			500	µA
C_i	V_I = V_{CC} or GND	3.3V		5		pF

(1) T_A = 25°C

5.7 Electrical Characteristics, SN74LVC08A

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	SN74LVC08A						UNIT
			T_A = 25°C			–40°C to +85°C		–40°C to +125°C	
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V_{OH}	I_{OH} = –100 µA	1.65V to 3.6V	V_{CC} – 0.2			V_{CC} – 0.2		V_{CC} – 0.3		V
	I_{OH} = –4 mA	1.65V	1.29			1.2		1.05		
	I_{OH} = –8 mA	2.3V	1.9			1.7		1.55		
	I_{OH} = –12 mA	2.7V	2.2			2.2		2.05		
		3V	2.4			2.4		2.25		
	I_{OH} = –24 mA	3V	2.3			2.2		2		
V_{OL}	I_{OL} = 100 µA	1.65V to 3.6V			0.1		0.2		0.3	V
	I_{OL} = 4 mA	1.65V			0.24		0.45		0.6	
	I_{OL} = 8 mA	2.3V			0.3		0.7		0.75	
	I_{OL} = 12 mA	2.7V			0.4		0.4		0.6	
	I_{OL} = 24 mA	3V			0.55		0.55		0.8	
I_I	V_I = 5.5 V or GND	3.6V			±1		±5		±20	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6V			1		10		40	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7V to 3.6V			500		500		5000	µA
C_i	V_I = V_{CC} or GND	3.3V		5						pF

5.8 Switching Characteristics, SN54LVC08A

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	SN54LVC08A		UNIT
				–55°C to +125°C		
				MIN	MAX	
t_{pd}	A or B	Y	2.7V		4.8	ns
			3.3V ± 0.3V	1	4.1	

5.9 Switching Characteristics, SN74LVC08A

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	SN74LVC08A							UNIT
				T_A = 25°C			–40°C to +85°C		–40°C to +125°C		
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1.8V ± 0.15V	1	5	9.3	1	9.8	1	11.3	ns
			2.5V ± 0.2V	1	2.9	6.4	1	6.9	1	9	
			2.7V	1	3	4.6	1	4.8	1	6	
			3.3V ± 0.3V	1	2.6	3.9	1	4.1	1	5.5	
$t_{sk(o)}$			3.3V ± 0.3V					1		1.5	ns

5.10 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	f = 10 MHz	1.8 V	7	pF
			2.5 V	9.8	
			3.3 V	10	

5.11 Typical Characteristics

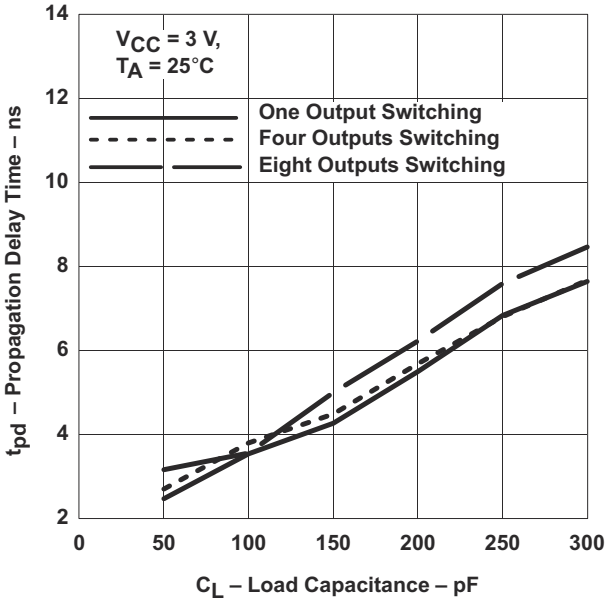


Figure 5-1. Propagation Delay (Low to High Transition) vs Load Capacitance

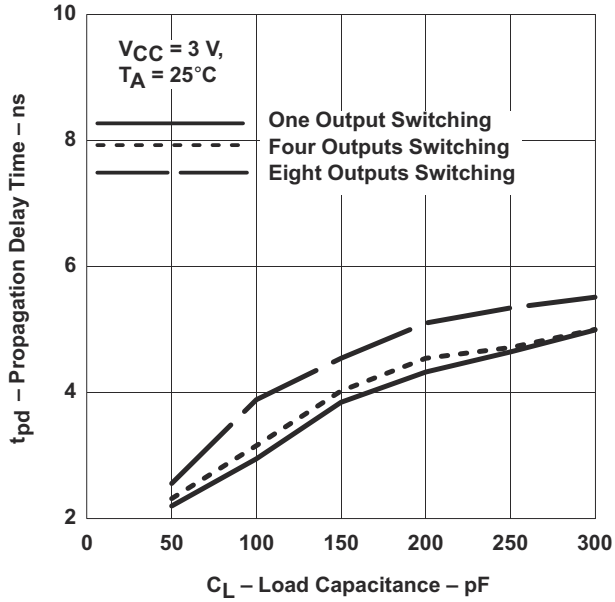
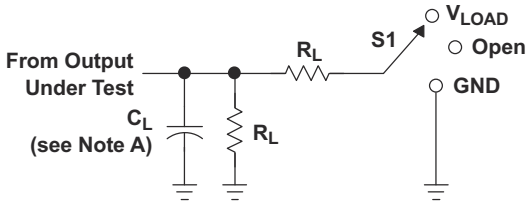


Figure 5-2. Propagation Delay (High to Low Transition) vs Load Capacitance

6 Parameter Measurement Information

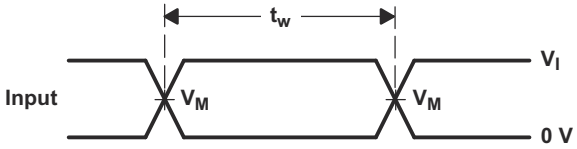
Load Circuit and Voltage Waveforms



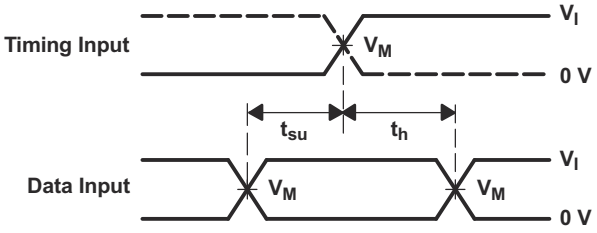
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

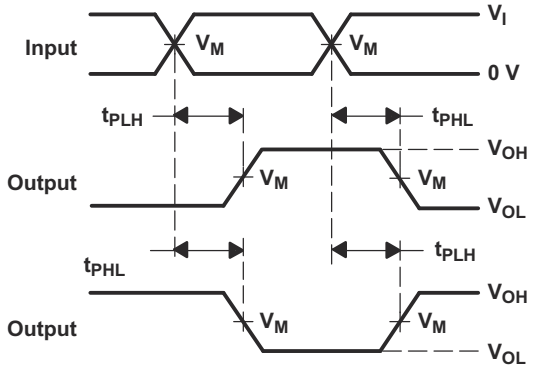
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_D
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	500 Ω	0.15 V
2.7 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
3.3 V ± 0.3 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V



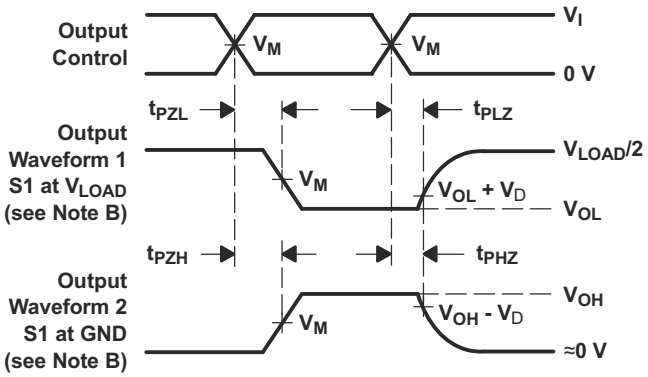
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR≤ 10 MHz, Z_O = 50 W.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

7 Detailed Description

7.1 Overview

The SN74LVC08 device contains four 2-input positive AND gate device and performs the Boolean function Y = A × B. This device is useful when multiple AND function is used in the system.

7.2 Functional Block Diagram

Figure 7-1. Logic Diagram, Each Gate (Positive Logic)

7.3 Feature Description

7.3.1 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the power output of the device to be limited to avoid thermal runaway and damage due to over-current. The electrical and thermal limits defined the in the *Section 5.1* must be followed at all times.

7.3.2 Standard CMOS Inputs

Standard CMOS inputs are high impedance and are typically modelled as a resistor in parallel with the input capacitance given in the *Section 5.6* and *Section 5.7*. The worst case resistance is calculated with the maximum input voltage, given in the *Section 5.1*, and the maximum input leakage current, given in the*Section 5.6* and *Section 5.7*, using ohm's law (R = V ÷ I).

Signals applied to the inputs need to have fast edge rates, as defined by Δt/Δv in *Section 5.3* and *Section 5.4* to avoid excessive currents and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be utilized to condition the input signal prior to the standard CMOS input.

7.3.3 Clamp Diodes

The inputs to this device have negative clamping diodes. The outputs to this device have both positive and negative clamping diodes as shown in Figure 7-2.

CAUTION

Voltages beyond the values specified in the *Section 5.1* table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

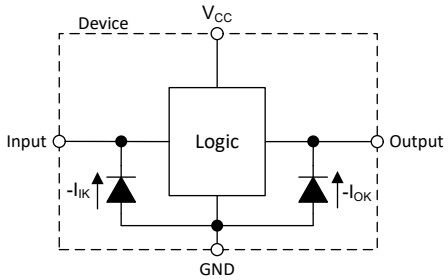


Figure 7-2. Electrical Placement of Clamping Diodes for Each Input and Output

7.3.4 Over-voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in the *Section 5.1*.

7.4 Device Functional Modes

Table 7-1 lists the functional modes for the SN54LVC08A and SN74LVC08A devices.

Table 7-1. Truth Table

INPUTS		OUTPUT
A	**B**	**Y**
L	L	L
L	H	L
H	L	L
H	H	H

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The SN74LVC08A is used to drive CMOS device and used for implementing AND logic. The LVC family can support current drive of about 24 mA at 3-V V_{CC}. The inputs for SN74LVC08A are 5.5-V tolerant allowing it to translate down to V_{CC}.

8.2 Typical Application

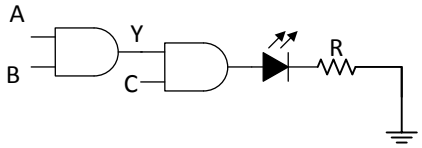


Figure 8-1. Three Input AND Gate Implementation and Driving LED

8.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

8.2.2 Detailed Design Procedure

SN74LVC08A contains four AND gates in one package which can be used for individual AND function or to implement complex Boolean logic. Figure 8-1 shows an example of implementing 3input AND function. AB are inputs for AND gate which are connected to another AND gate. Z= A × B × C. SN74LVC08A support high drive current of 24 mA which can be used to drive LEDs of even Drive low current signal FETs, an example is shown in Figure 8-1 TI recommends to use a series resistance to limit the current. If V_{CC} is 3 V, and LED current should be 10 mA, and the forward-voltage of LED is 2.5 V, then R as shown in Figure 8-1 is calculated using Equation 1:

$$R = (V_{CC} – V_{LED}) / I \quad (1)$$

$$R = (3 – 2.5) / 0.01 = 50\ \Omega$$

8.2.3 Application Curves

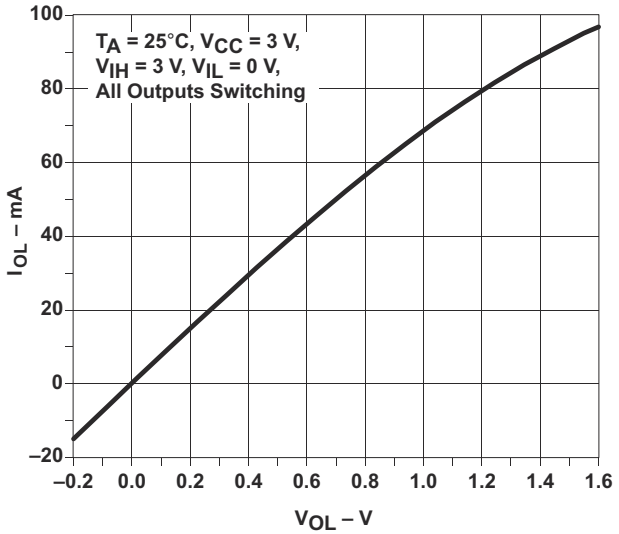


Figure 8-2. Output Drive Current (I_{OL}) vs LOW-level Output Voltage (V_{OL})

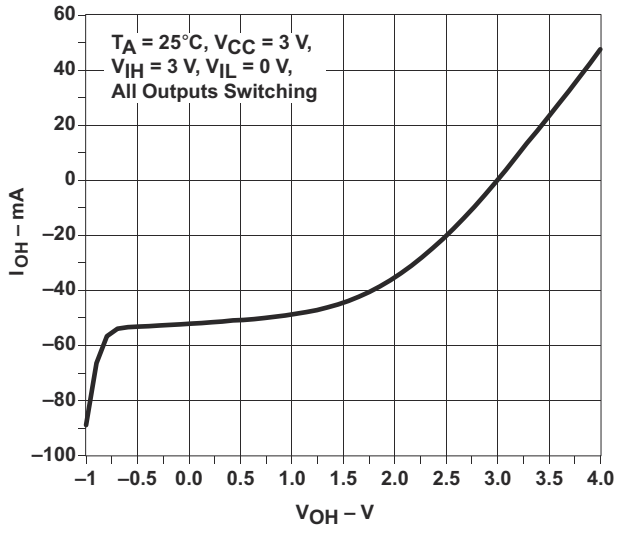


Figure 8-3. Output Drive Current (I_{OH}) vs HIGH-level Output Voltage (V_{OH})

Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions* table.

The V_{CC} pin must have a good bypass capacitor to prevent power disturbance. TI recommends to use a 0.1-µF capacitor. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

8.3 Layout

8.3.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in Figure 8-4 are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or VCC, whichever makes more sense or is more convenient.

Even low data rate digital signals can have high frequency signal components due to fast edge rates. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 8-5 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

8.3.2 Layout Examples

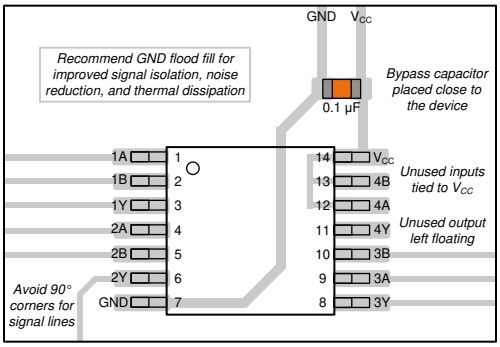


Figure 8-4. Example Layout

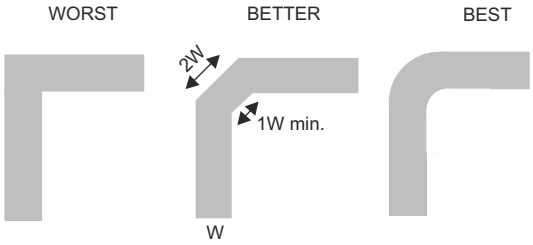


Figure 8-5. Trace Example

9 Device and Documentation Support

9.1 Documentation Support (Analog)

9.1.1 Related Documentation

For related documentation see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004

9.1.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to order now.

Table 9-1. Related Links

PARTS	PRODUCT FOLDER	ORDER NOW	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
SN54LVC08A	Click here	Click here	Click here	Click here	Click here
SN74LVC08A	Click here	Click here	Click here	Click here	Click here

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.3.1 Community Resources

9.4 Trademarks

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9.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary — This glossary lists and explains terms, acronyms, and definitions.

10

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision U (March 2024) to Revision V (May 2024)	Page
• Updated RθJA values: DB = 112.8 to 140.4, PW = 127.7 to 150.8, RGY = 51.1 to 92.1, NS = 95.1 to 123.8; updated DB, PW, RGY, and NS packages for RθJC(top), RθJB, ΨJT, ΨJB, and RθJC(bot), all values in °C/W	6

Changes from Revision T (July 2019) to Revision U (March 2024)	Page
• Updated the structural layout of data sheet	1
• Added BQA package to *Device Information* table	1
• Added BQA package to *Pin Configuration and Functions* section	3
• Removed Machine Model from *Features* section and *ESD Ratings* table	5
• Added BQA package to *Thermal Information* table	6
• Updated *Layout Example*	15

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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